

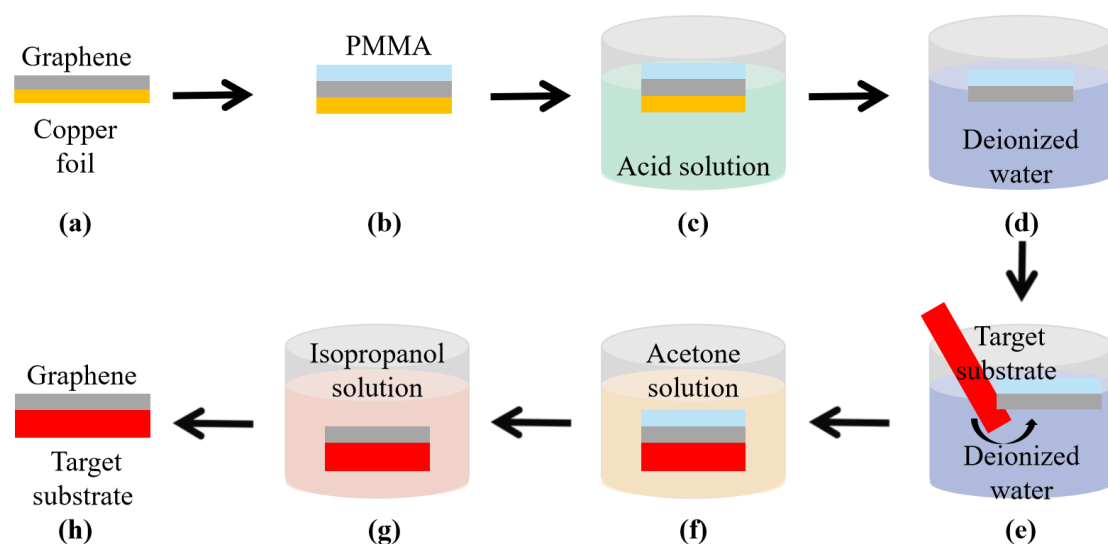
Electronic supplementary information (ESI)

## Dual-wavelength visible photodetector based on vertical (In,Ga)N nanowires grown by molecular beam epitaxy

Jianya Zhang,<sup>ab</sup> Min Zhou,<sup>ab</sup> Dongmin Wu,<sup>ab</sup> Lifeng Bian,<sup>ab</sup> Yukun Zhao,<sup>\*a</sup>  
Hua Qin,<sup>ab</sup> Wenxian Yang,<sup>a</sup> Yuanyuan Wu,<sup>a</sup> Zhiwei Xing<sup>ab</sup> and Shulong Lu<sup>\*ab</sup>

<sup>a</sup> Suzhou Institute of Nano-Tech and Nano-Bionics (SINANO), Chinese Academy of Sciences (CAS),  
215123 Suzhou, China. E-mail: ykzhao2017@sinano.ac.cn, sllu2008@sinano.ac.cn

<sup>b</sup> School of Nano-Tech and Nano-Bionics, University of Science and Technology of China, 230026  
Hefei, China



**Fig. S1** Schematic illustration of transferring graphene from the copper foil to target substrate (nanowire sample). (a) The graphene grown on copper foil. (b) Spin coating the polymethyl methacrylate (PMMA) on the top of graphene. (c) Etch copper foil by acid solution. (d) Clean graphene by deionized water. (e) Transfer graphene to the top of nanowires. (f) Dissolve PMMA by acetone solution. (g) Dissolve acetone by isopropanol solution. (h) Clean graphene by deionized water and dry it by nitrogen.